

1.5V Drive Pch MOSFET

RAL025P01

Structure

Silicon P-channel MOSFET

Features

- 1) Low On-resistance.
- 2) Small high power package.
- 3) Low voltage drive.(1.5V)

Application

Switching

Packaging specifications

| Type | Package | Taping |
|----------|------------------------------|--------|
| | Code | TCR |
| | Basic ordering unit (pieces) | 3000 |
| RAL025P0 | 0 | |

● Absolute maximum ratings (Ta = 25°C)

| Parameter | | Symbol | Limits | Unit |
|------------------------------|------------|--------------------|-------------|------|
| Drain-source voltage | | V_{DSS} | -12 | V |
| Gate-source voltage | | V_{GSS} | 0 to -8 | V |
| Drain current | Continuous | I _D | ±2.5 | Α |
| | Pulsed | I _{DP} *1 | ±6 | Α |
| Source current | Continuous | I _S | -0.8 | Α |
| (Body Diode) | Pulsed | I _{SP} *1 | -6 | Α |
| Power dissipation | | P _D *2 | 1 | W |
| Channel temperature | | Tch | 150 | °C |
| Range of storage temperature | | Tstg | -55 to +150 | °C |

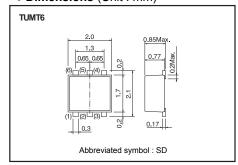
^{*1} Pw≤10µs, Duty cycle≤1%

● Thermal resistance

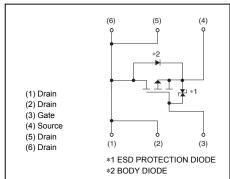
| Parameter | Symbol | Limits | Unit |
|--------------------|-------------|--------|------|
| Channel to Ambient | Rth (ch-a)* | 125 | °C/W |

^{*}Mounted on a ceramic board.

● Dimensions (Unit : mm)



• Inner circuit



^{*2} Mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions | |
|---------------------------------|-----------------------|------|------|------|----------|---|--|
| Gate-source leakage | I_{GSS} | - | - | -10 | μA | V_{GS} =-8V, V_{DS} =0V | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | -12 | - | - | ٧ | I _D =-1mA, V _{GS} =0V | |
| Zero gate voltage drain current | I _{DSS} | - | - | -10 | μA | V_{DS} =-12V, V_{GS} =0V | |
| Gate threshold voltage | V _{GS (th)} | -0.3 | 1 | -1.0 | V | V_{DS} =-6V, I_D =-1mA | |
| | | • | 44 | 62 | | I _D =-2.5A, V _{GS} =-4.5V | |
| Static drain-source on-state | R * | - | 55 | 77 | mΩ | I _D =-1.2A, V _{GS} =-2.5V | |
| resistance | R _{DS (on)} | - | 75 | 110 | 1115.2 | I _D =-1.2A, V _{GS} =-1.8V | |
| | | - | 90 | 180 | | I _D =-0.5A, V _{GS} =-1.5V | |
| Forward transfer admittance | I Y _{fs} ľ | 3.5 | - | - | S | I _D =-2.5A, V _{DS} =-6V | |
| Input capacitance | C _{iss} | - | 2000 | - | pF | V _{DS} =-6V | |
| Output capacitance | C _{oss} | - | 130 | - | pF | V _{GS} =0V | |
| Reverse transfer capacitance | C _{rss} | - | 120 | - | pF | f=1MHz | |
| Turn-on delay time | t _{d(on)} * | - | 11 | - | ns | I _D =-1.2A, V _{DD} ≒ -6V | |
| Rise time | t _r * | - | 40 | - | ns | V _{GS} =-4.5V | |
| Turn-off delay time | t _{d(off)} * | - | 160 | - | ns | $R_L=5\Omega$ | |
| Fall time | t _f * | - | 60 | - | ns | R_G =10 Ω | |
| Total gate charge | Q _g * | - | 16 | - | nC | I _D =-2.5A | |
| Gate-source charge | Q _{gs} * | - | 2.4 | - | nC | V _{DD} ≒–6V | |
| Gate-drain charge | Q _{gd} * | - | 2.2 | - | nC | V _{GS} =-4.5V | |

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|-------------------|------|------|------|------|--|
| Forward Voltage | V _{SD} * | - | - | -1.2 | V | I _s =-2.5A, V _{GS} =0V |

^{*}Pulsed

●Electrical characteristic curves (Ta=25°C)

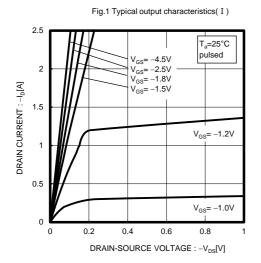


Fig.3 Typical Transfer Characteristics

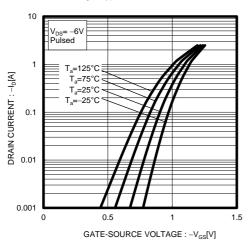


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

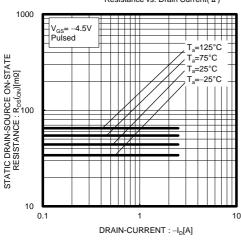


Fig.2 Typical output characteristics(${\rm I\hspace{-.1em}I}$) 2.5 T_a=25°C pulsed 2 DRAIN CURRENT: -I_D[A] 1.5 V_{GS}= −4.5V $V_{GS} = -2.5V$ $V_{GS} = -1.8V$ 1 V_{GS}= -1.5V 0.5 $V_{GS} = -1.0V$ 0 0 4 6 10 DRAIN-SOURCE VOLTAGE : $-V_{DS}[V]$

Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

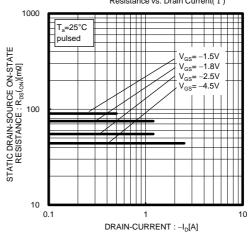
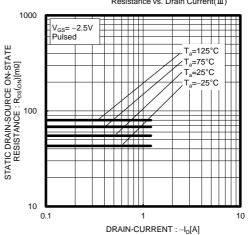
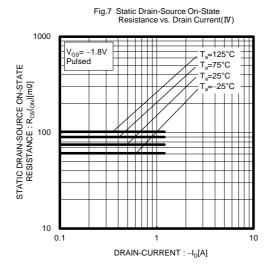
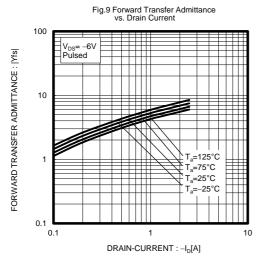
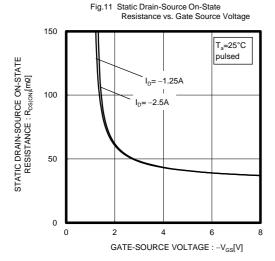


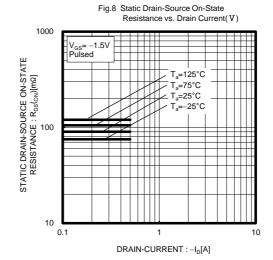
Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

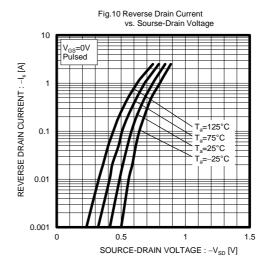


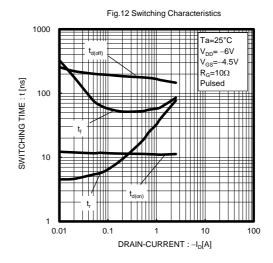


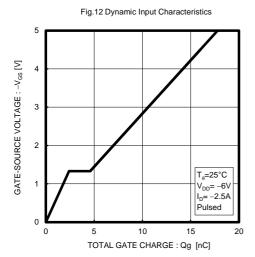


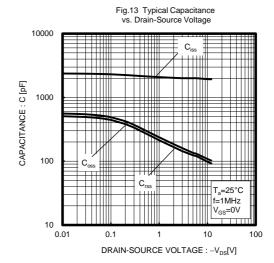












Measurement circuits

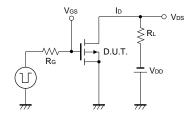


Fig.1-1 Switching Time Measurement Circuit

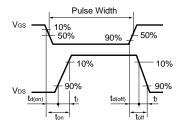


Fig.1-2 Switching Waveforms

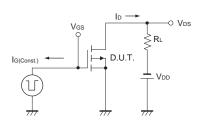


Fig.2-1 Gate Charge Measurement Circuit

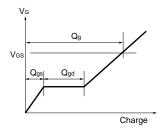


Fig.2-2 Gate Charge Waveform

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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